

AMENDMENTS TO THE SPECIFICATION

At page 7, after line 25 insert:

FIG.26 is a structural drawing showing a third embodiment of the present invention.

Replace the paragraph beginning at page 20, line 23 with:

In this embodiment, the configuration of a semiconductor laser device is similar to as the embodiment shown in Fig. 1. However, in addition to the four-layered low reflective reflectivity film as described above, as in the embodiment shown in Fig. 26, the low reflectivity multilayer dielectric film 10, in combination with a fifth dielectric film 21 and a sixth dielectric film 22, which form another film 23, partly formed in covering a region of the low reflectivity multilayer dielectric film 10, other than a light emitting point, so that. The low reflectivity multilayer dielectric film 10 and the film 17 form another film having a lower reflective film reflectivity, where that is, a reflectance is smaller than the reflectance of the region of the low reflectivity multilayer dielectric film 10 covering the light emitting point, is obtained.